

AMENDMENTS TO THE SPECIFICATION:

Please amend the paragraph beginning at page 4, line 17, as follows:

For the film formation, gases containing the starting materials are introduced through the gas introduction ports 105 and 106 into a space between the ceiling plate 102 and the upper ends of the partition plates 104 and mixed together. The resulting mixed gas G is ~~blown~~ discharged downward along the partition plates 104 and supplied to the surface of the silicon substrate 21 that travels below the assembly 101 while being conveyed by a conveyor belt 23. This gas G decomposes on the surface of the silicon substrate 21 and forms a film having a composition that corresponds to the kinds of the starting materials on the surface of the silicon substrate 21. The remaining gas is exhausted ~~discharged~~ from an exhaust port 110 to the outside through a gap 109 between the assembly 101 and a cover protuberance 108.

Please amend the paragraph beginning at page 16, line 7, as follows:

In the apparatus shown in Fig. 3, the silicon substrate 1 is first pre-heated by a pre-heater 2 and conveyed by a conveyor belt 3 to a film formation position 13. In the film formation position 13, a heater 4 sets the film formation temperature. The titanium compound and the compound of the dopant element, both in a gaseous state, are passed through gas lines 7 and 8, respectively, and supplied to the surface of the silicon substrate 1 from a dispersion head 5. The titanium compound and the compound of the dopant element thus supplied are thermally decomposed on the surface of the silicon substrate 1, forming a titanium oxide film. In the apparatus shown in Fig. 3, the conveyor belt 3 conveys the silicon substrate 1 from the position immediately below the discharge port of the gas line 7 of the dispersion head 5 for the compound of the dopant element, through the position immediately below the discharge port of the gas line

8 for the titanium compound to the position immediately below the discharge port for the atmospheric gas of the gas line 9.

Please amend the paragraph beginning at page 17, line 6, as follows:

In the film formation position ~~portion~~ 13, exhaust gas that comprises the carrier gas, the dilution gas, the undecomposed starting materials and the decomposition product ~~products~~ is exhausted ~~discharged~~ from both sides of the dispersion head 5 to an exhaust port 12.